

GENERAL DESCRIPTION

The 0912GN-650V is an internally matched, COMMON SOURCE, class AB GaN on SiC HEMT transistor capable of providing over 17dB gain, 650 Watts of pulsed RF output power at 128 μ s pulse width, 10% duty factor across the 960 to 1215 MHz band. The transistor has internal pre-match for optimal performance. This hermetically sealed transistor can be used for Broadband Avionics Data Link applications. It utilizes gold metallization and eutectic attach to provide highest reliability and superior ruggedness.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation

Device Dissipation @ 25°C 1400 W

Maximum Voltage and Current

Drain-Source Voltage (V_{DSS}) 150 V

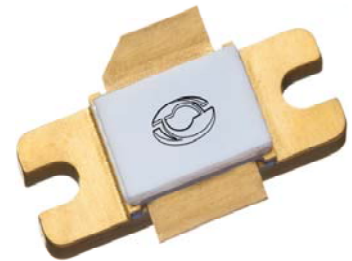
Gate-Source Voltage (V_{GS}) -8 to +0 V

Maximum Temperatures

Storage Temperature (T_{STG})-55 to +125 °C

Operating Junction Temperature +250 °C

CASE OUTLINE 55-KR Common Source



ELECTRICAL CHARACTERISTICS @ 25°C

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
Pout	Output Power	Freq=960, 1090, 1215 MHz	650			W
Gp	Power Gain	Pout=650W, Freq=960, 1090, 1215 MHz	17	18		dB
η_d	Drain Efficiency	Pout=650W, Freq=960, 1090, 1215 MHz	48	53		%
Dr	Droop	Pout=650W, Freq=960, 1090, 1215 MHz			0.8	dB
VSWR-T	Load Mismatch Tolerance	Pout=650W, Freq= 1215MHz			3:1	
θ_{jc}	Thermal Resistance	Pulse Width=128 μ s, Duty=10%			0.155	°C/W

- Bias Condition: $V_{dd}=+50V$, $I_{dq}=100mA$ average current ($V_{gs}= -2.0 \sim -4.5V$) with constant gate bias

FUNCTIONAL CHARACTERISTICS @ 25°C

$I_{D(Off)}$	Drain leakage current	$V_{gs} = -8V$, $V_D = 150V$			64	mA
$I_{G(Off)}$	Gate leakage current	$V_{gs} = -8V$, $V_D = 0V$			22	mA
BV_{DSS}	Drain-source breakdown voltage	$V_{gs} = -8V$, $I_D = 64mA$	150			V

Issue June 2013

Export Classification: EAR-99

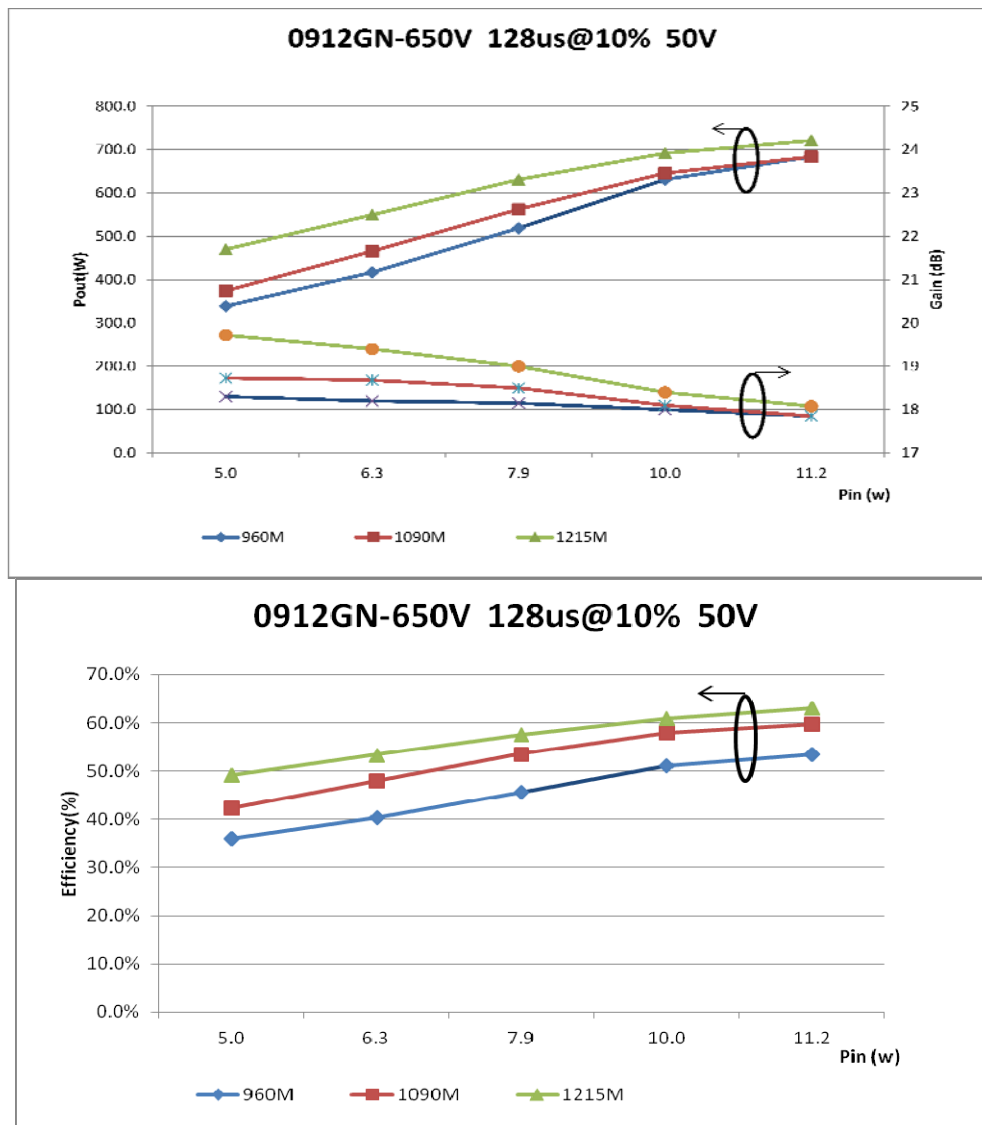
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Specifications are subject to change, consult the RFIS factory at (408) 986-8031 for the latest information

0912GN-650V

650 Watts - 50 Volts, 128 μ s, 10%
Broad Band Data Link 960 - 1215 MHz

TYPICAL BROAD BAND PERFORMANCE DATA

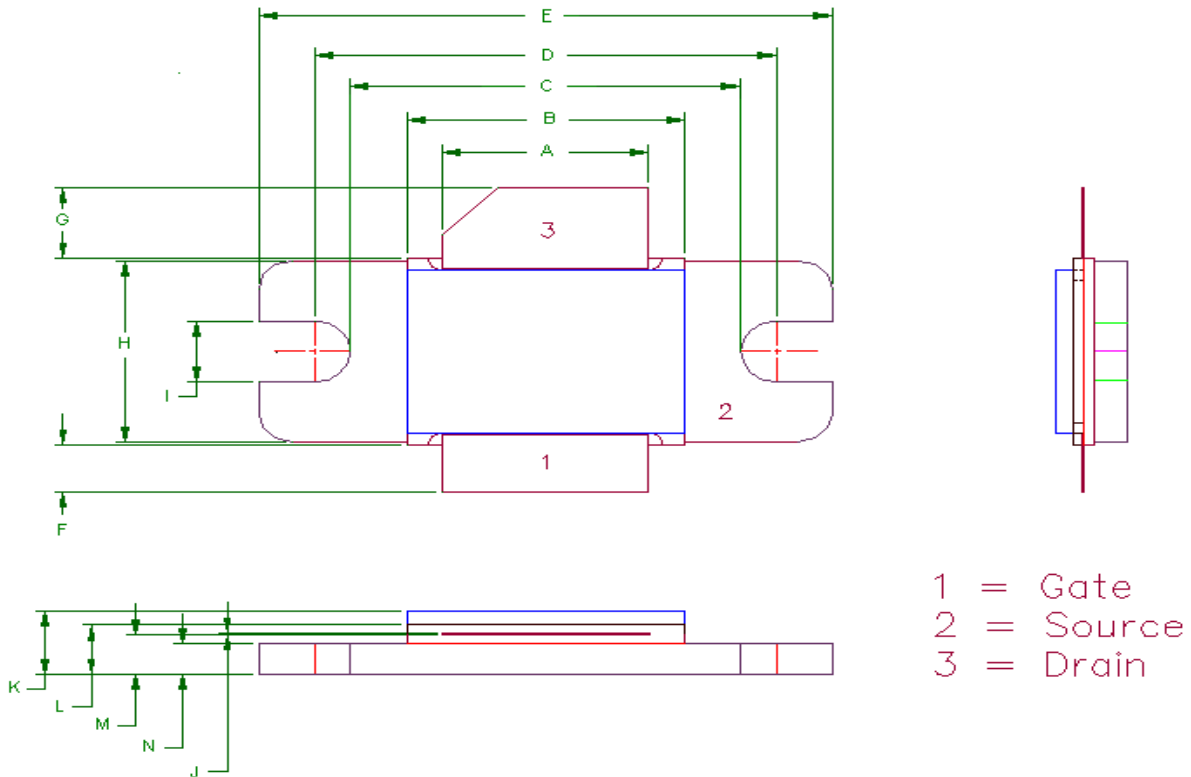
Frequency	Pin (W)	Pout (W)	Id (A)	RL (dB)	Eff (%)	G (dB)	Drop (dB)
960 MHz	11.2	684	2.56	-7	53	17.9	0.3
1090 MHz	11.2	684	2.29	-7	60	17.9	0.3
1215 MHz	11.2	721	2.29	-14	63	18.1	0.4



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55-KR PACKAGE DIMENSION



Dimension	Min (mil)	Min (mm)	Max (mil)	Max (mm)
A	370	9.40	372	9.44
B	498	12.65	500	12.7
C	700	17.78	702	17.83
D	830	21.08	832	21.13
E	1030	26.16	1032	26.21
F	101	2.56	102	2.59
G	151	3.84	152	3.86
H	385	9.78	387	9.83
I	130	3.30	132	3.35
J	003	.076	004	0.10
K	135	3.43	137	3.48
L	105	2.67	107	2.72
M	085	2.16	86	2.18
N	065	1.65	66	1.68



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Revision History

Revision Level / Date	Para. Affected	Description
01 / June 2013	-	Initial Preliminary Release

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